Silicon NPN Epitaxial

HITACHI

ADE-208-013A (Z) 2nd. Edition Mar. 2001

Application

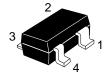
VHF / UHF wide band amplifier

Features

- High gain bandwidth product
 f_T = 11 GHz Typ
- High gain, low noise figure
 PG = 16.5 dB Typ, NF = 1.1 dB Typ at f = 900 MHz

Outline

CMPAK-4



- 1. Collector
- 2. Emitter
- 3. Base
- 4. Emitter

Note: Marking is "YD-".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

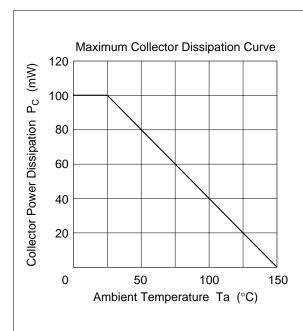


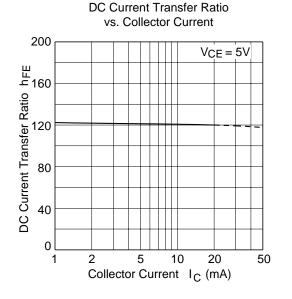
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

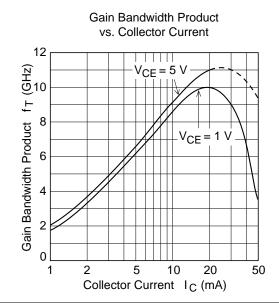
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V _{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

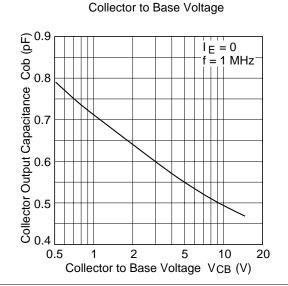
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltge	$V_{(BR)CBO}$	15	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}	_	_	10	μΑ	V _{CB} = 12 V, I _E = 0
	I _{CEO}	_	_	1	mA	V _{CE} = 8 V, R _{BE} = ∞
Emitter cutoff current	I _{EBO}	_	_	10	μΑ	$V_{EB} = 1.5 \text{ V}, I_{C} = 0$
DC current transfer ratio	h_{FE}	50	120	250		$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Collector output capacitance	Cob	_	0.55	1.05	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Gain bandwidth product	f _T	8.0	11.0	_	GHz	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
S21 Parameter	S21	_	16	_	dB	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA},$ f = 1000 MHz
Power gain	PG	13.5	16.5	_	dB	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.1	2.0	dB	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA},$ f = 900 MHz

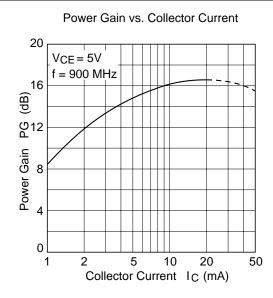




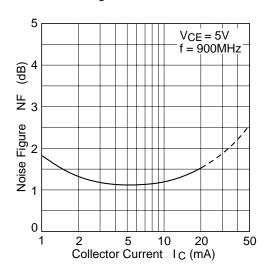




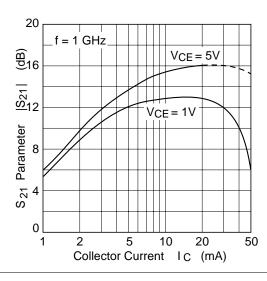
Collector Output Capacitance vs.



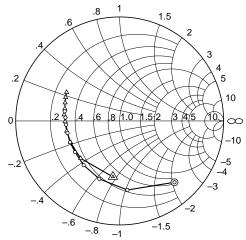
Noise Figure vs. Collector Current



S21 Parameter vs. Collector Current

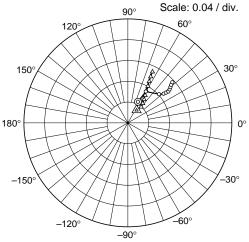


S11 Parameter vs. Frequency



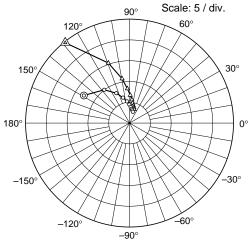
Condition: $V_{CE}=5$ V , $Z_{O}=50$ Ω 200 to 2000 MHz (200 MHz step) Ω (IC = 5 mA) Ω (IC = 20 mA)

S12 Parameter vs. Frequency



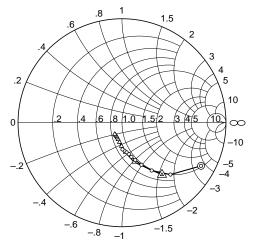
Condition: $V_{CE} = 5 \text{ V}$, $Z_{O} = 50 \Omega$ 200 to 2000 MHz (200 MHz step) \bigcirc (IC = 5 mA) \triangle (IC = 20 mA)

S21 Parameter vs. Frequency



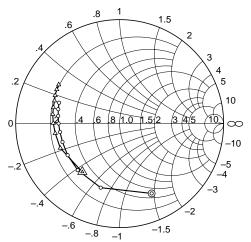
Condition: $V_{CE} = 5 \text{ V}$, $Z_{O} = 50 \Omega$ 200 to 2000 MHz (200 MHz step) \bigcirc (I $_{C} = 5 \text{ mA}$) \triangle $_{\Delta}$ (I $_{C} = 20 \text{ mA}$)

S22 Parameter vs. Frequency

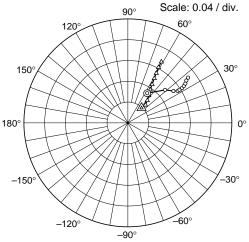


Condition: $V_{CE} = 5 \text{ V}$, $Z_0 = 50 \Omega$ 200 to 2000 MHz (200 MHz step) \bigcirc (I C = 5 mA) \triangle (I C = 20 mA)

S11 Parameter vs. Frequency

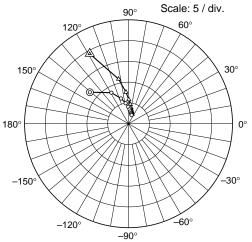


S12 Parameter vs. Frequency

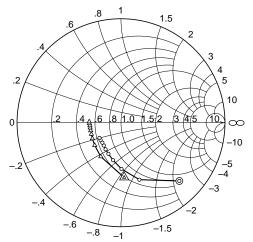


Condition: $V_{CE}=1~V$, $Z_{O}=50~\Omega$ 200 to 2000 MHz (200 MHz step) \bigcirc (I C = 5 mA) \triangle (I C = 20 mA)

S21 Parameter vs. Frequency



S22 Parameter vs. Frequency



Condition: $V_{CE}=1~V$, $Z_0=50~\Omega$ 200 to 2000 MHz (200 MHz step) \bigcirc (IC = 5 mA) \triangle (IC = 20 mA)

S Parameter (V $_{CE}$ = 5 V, I_{C} = 5 mA, Z_{O} = 50 $\Omega)$

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.781	-48.2	12.84	148.8	0.0449	64.6	0.866	-28.6
400	0.669	-83.6	10.04	127.3	0.0695	50.3	0.682	-46.9
600	0.591	-109.4	7.84	113.9	0.0815	42.6	0.541	-58.1
800	0.549	-129.1	6.30	104.4	0.0889	39.2	0.446	-65.2
1000	0.524	-145.0	5.23	96.7	0.0937	38.4	0.381	-70.4
1200	0.520	-156.8	4.45	90.7	0.0986	37.7	0.340	-74.6
1400	0.515	-166.9	3.86	86.0	0.103	38.7	0.309	-77.7
1600	0.518	-176.0	3.44	81.1	0.107	40.0	0.287	-81.2
1800	0.523	176.5	3.11	77.3	0.111	41.2	0.268	-85.1
2000	0.537	170.1	2.82	73.5	0.116	42.4	0.256	-89.0

S Parameter (V $_{CE}$ = 5 V, I_{C} = 20 mA, Z_{O} = 50 $\Omega)$

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.542	-69.9	24.74	128.7	0.0296	55.5	0.631	-52.5
400	0.520	-136.2	15.31	109.4	0.0398	50.2	0.395	-72.9
600	0.516	-156.3	10.81	99.5	0.0470	52.8	0.285	-83.6
800	0.519	-169.1	8.29	93.5	0.0547	55.1	0.225	-91.3
1000	0.525	-179.2	6.70	88.5	0.0624	57.9	0.189	-97.5
1200	0.538	173.6	5.63	84.1	0.0712	60.2	0.166	-102.8
1400	0.540	167.5	4.85	80.9	0.0805	61.5	0.151	-107.9
1600	0.554	161.6	4.29	77.5	0.0895	62.8	0.140	-112.6
1800	0.567	159.5	3.86	74.3	0.0991	63.8	0.134	-118.1
2000	0.580	151.7	3.48	71.6	0.109	64.3	0.129	-122.5

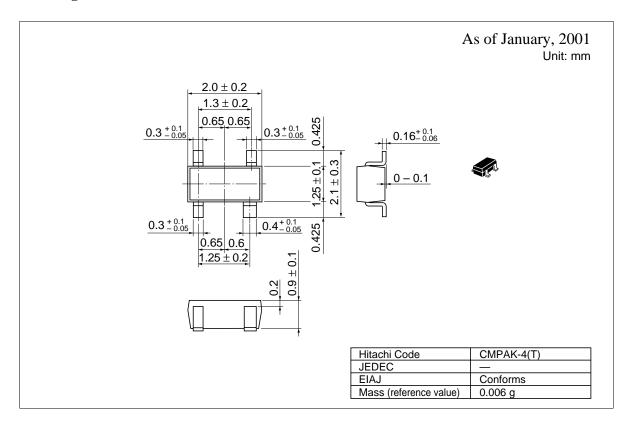
S Parameter (V $_{CE}$ = 1 V, I_{C} = 5 mA, Z_{O} = 50 $\Omega)$

Freq.	S 11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.739	-65.4	11.99	140.8	0.0681	56.9	0.793	-44.9
400	0.643	-106.5	8.54	118.9	0.0957	41.5	0.576	-72.1
600	0.603	-132.0	6.34	106.4	0.107	34.9	0.446	-89.4
800	0.586	-148.7	4.99	97.9	0.114	32.6	0.369	-101.9
1000	0.578	-162.1	4.08	90.9	0.118	32.6	0.323	-112.0
1200	0.580	-171.9	3.45	86.0	0.124	32.7	0.396	-120.1
1400	0.588	179.9	2.99	81.7	0.129	33.3	0.275	-127.0
1600	0.596	172.9	2.67	77.2	0.134	34.3	0.263	-133.0
1800	0.607	166.8	2.41	73.4	0.139	35.9	0.256	-139.5
2000	0.617	161.0	2.20	70.0	0.145	36.9	0.254	-144.7

S Parameter (V $_{CE}=1$ V, $I_{C}=20$ mA, $Z_{O}=50~\Omega)$

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.588	-127.7	19.25	119.0	0.0389	47.2	0.527	-86.7
400	0.618	-157.6	11.00	102.5	0.0483	45.3	0.380	-120.8
600	0.627	-171.4	7.62	94.6	0.0570	49.0	0.334	-139.3
800	0.639	179.6	5.80	89.2	0.0662	52.6	0.315	-150.9
1000	0.650	172.1	4.66	84.5	0.0768	55.9	0.306	-158.9
1200	0.656	-166.4	3.94	81.1	0.873	57.7	0.302	-165.4
1400	0.664	160.7	3.40	78.2	0.0996	59.2	0.301	-170.5
1600	0.677	156.5	3.03	75.2	0.110	60.2	0.301	-174.6
1800	0.689	151.6	2.71	71.9	0.122	61.1	0.304	-178.4
2000	0.696	147.5	2.47	69.2	0.134	61.2	0.306	178.2

Package Dimensions



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